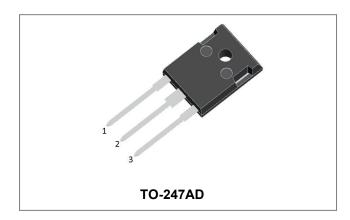


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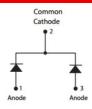
## STW80H150C SCHOTTKY RECTIFIER



# Features

- 175 °C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	150	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=150°C, rectangular wave form	40(Per Leg) 80(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	Ігѕм	8.3ms, Half Sine pulse	280	А

# **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	$V_{F1}$	@ 40A, Pulse, T <sub>J</sub> = 25℃	-	0.91	V
	$V_{F2}$	@ 40A, Pulse, T <sub>J</sub> = 125℃	-	0.76	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> ,T <sub>J</sub> = 25℃	-	0.3	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> ,T <sub>J</sub> = 125℃	-	48	mA
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^{*}</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%

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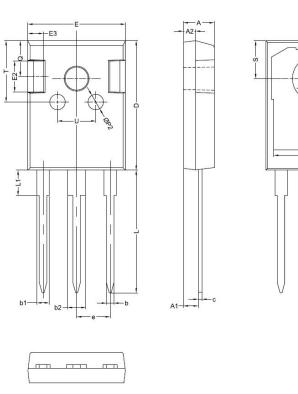


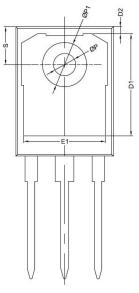


## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>θ</sub> JC	DC operation	0.7	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

### **Mechanical Dimensions TO-247AD**





	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
Е	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S T	6.05	6.15	6.25		
Т		10.00			
J		6.20			

# **Ordering Information:**

Device	Package	Shipping	
STW80H150C	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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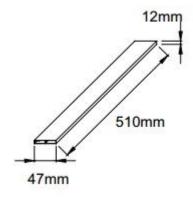


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#### Tube Specification



#### **Marking Diagram**



#### Where XXXXX is YYWWL

= Device Type = Ultralow VF W = Package type = Forward Current (80A) 80 = Tj 175°C 150 = Reverse Voltage (150V) = Configuration SSG = SSG = Year ww = Week = Lot Number Cautions: Molding resin Epoxy resin UL:94V-0

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